Low-power dual 2-input NAND gate Rev. 10 — 3 July 2017

Product data sheet

#### **General description** 1

The 74AUP2G00 provides dual 2-input NAND function.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

#### Features and benefits 2

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- · Complies with JEDEC standards:
  - JESD8-12 (0.8 V to 1.3 V)
  - JESD8-11 (0.9 V to 1.65 V)
  - JESD8-7 (1.2 V to 1.95 V)
  - JESD8-5 (1.8 V to 2.7 V)
  - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5 000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1 000 V
- Low static power consumption;  $I_{CC} = 0.9 \ \mu A$  (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

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# **3** Ordering information

Table 1. Ordering	information								
Type number	Package	Package							
	Temperature range	Name	Description	Version					
74AUP2G00DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1					
74AUP2G00GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm	SOT833-1					
74AUP2G00GF	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm	SOT1089					
74AUP2G00GM	-40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 x 1.6 x 0.5 mm	SOT902-2					
74AUP2G00GN	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm	SOT1116					
74AUP2G00GS	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm	SOT1203					
74AUP2G00GX	-40 °C to +125 °C	X2SON8	plastic thermal enhanced extremely thin small outline package; no leads; 8 terminals; body 1.35 x 0.8 x 0.35 mm	SOT1233					

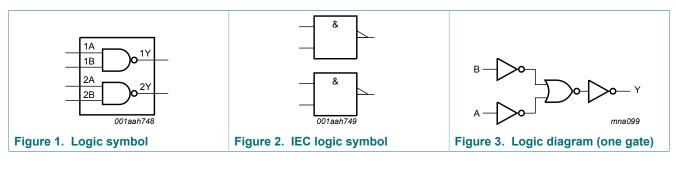
### 4 Marking

Table 2.	Marking	codes
	manning	0000

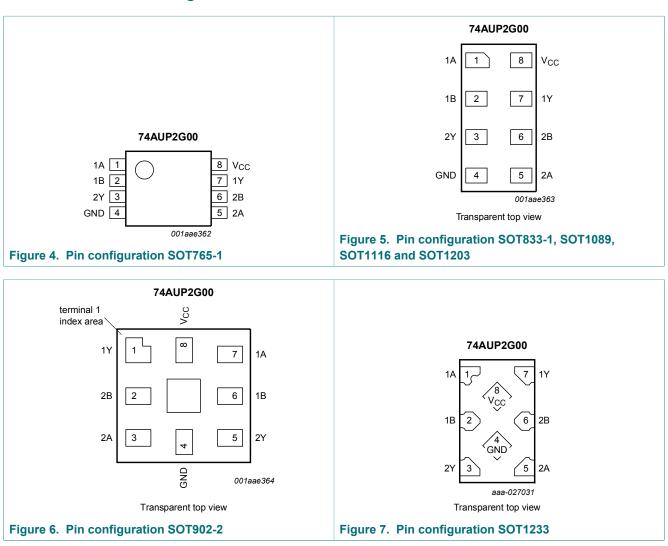
Type number	Marking code <sup>[1]</sup>
74AUP2G00DC	p00
74AUP2G00GT	p00
74AUP2G00GF	pA
74AUP2G00GM	p00
74AUP2G00GN	pA
74AUP2G00GS	pA
74AUP2G00GX	pA

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

### 5 Functional diagram



### 6 Pinning information



#### 6.1 Pinning

### 6.2 Pin description

Symbol	Pin		Description
	SOT765-1, SOT833-1, SOT1089, SOT1116, SOT1203 and SOT1233	SOT902-2	
1A, 2A	1, 5	7, 3	data input
1B, 2B	2, 6	6, 2	data input
GND	4	4	ground (0 V)
1Y, 2Y	7, 3	1, 5	data output
V <sub>CC</sub>	8	8	supply voltage

# 7 Functional description

Table 4. Function table <sup>[1]</sup>							
Input		Output					
nA	nB	nY					
L	L	Н					
L	Н	Н					
Н	L	Н					
Н	Н	L					

[1] H = HIGH voltage level;

L = LOW voltage level.

### 8 Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
VI	input voltage	[1]	-0.5	+4.6	V
Vo	output voltage	Active mode and Power-down mode [1]	-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < 0 V	-50	-	mA
I <sub>OK</sub>	output clamping current	V <sub>0</sub> < 0 V	-50	-	mA
I <sub>O</sub>	output current	$V_{O}$ = 0 V to $V_{CC}$	-	±20	mA
I <sub>CC</sub>	supply current		-	+50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C <sup>[2]</sup>	-	250	mW

The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 For VSSOP8 packages: above 110 °C the value of P<sub>tot</sub> derates linearly with 8.0 mW/K.

[2] For VSSOP8 packages: above 110 °C the value of P<sub>tot</sub> derates linearly with 8.0 mW/K. For XSON8 and XQFN8 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K. For X2SON8 package: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.7 mW/K.

### 9 Recommended operating conditions

#### Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>CC</sub>	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V <sub>CC</sub>	V
		Power-down mode; $V_{CC}$ = 0 V	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC}$ = 0.8 V to 3.6 V	-	200	ns/V

# **10 Static characteristics**

#### Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
T <sub>amb</sub> = 25	°C				1	
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	0.70 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
- amb = 25 /́IH /́IL /́OH /́OH /́OL /́OL /́OL		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.30 × V <sub>CC</sub>	V
′он		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC}$ = 3.0 V to 3.6 V	-	-	0.9	V
∕ <sub>он</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		$I_{O}$ = -20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.75 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.11	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.32	-	-	V
		$I_{\rm O}$ = -2.3 mA; $V_{\rm CC}$ = 2.3 V	2.05	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.72	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 µA; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
V <sub>OH</sub>     V <sub>OL</sub>         і і і оff		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.31	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	V
		$I_{\rm O}$ = 2.3 mA; $V_{\rm CC}$ = 2.3 V	-	-	0.31	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.44	V
		$I_{\rm O}$ = 2.7 mA; $V_{\rm CC}$ = 3.0 V	-	-	0.31	V
		$I_{O}$ = 4.0 mA; $V_{CC}$ = 3.0 V	-	-	0.44	V
I	input leakage current	$V_{I}$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	- 0.44	
OFF	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.2	μA
∆I <sub>OFF</sub>	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μA
сс	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ \text{to} \ 3.6 \ V \end{array}$	-	-	0.5	μA
∆I <sub>CC</sub>	additional supply current	$V_{I} = V_{CC} - 0.6 V; I_{O} = 0 A;$ [1 $V_{CC} = 3.3 V;$ per pin	- [[	-	40	μA

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# 74AUP2G00

### Low-power dual 2-input NAND gate

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
CI	input capacitance	$V_{CC}$ = 0 V to 3.6 V; V <sub>I</sub> = GND or V <sub>CC</sub>	-	0.8	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.7	-	pF
$T_{amb} = -4$	) °C to +85 °C				1	
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.30 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
V <sub>OH</sub>		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{\rm O}$ = -20 $\mu \text{A}; V_{\rm CC}$ = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.7 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.03	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.30	-	-	V
		$I_{\rm O}$ = -2.3 mA; $V_{\rm CC}$ = 2.3 V	1.97	-	-	V
		$I_{\rm O}$ = -3.1 mA; $V_{\rm CC}$ = 2.3 V	1.85	-	-	V
		$I_{\rm O}$ = -2.7 mA; $V_{\rm CC}$ = 3.0 V	2.67	-	-	V
		$I_{\rm O}$ = -4.0 mA; $V_{\rm CC}$ = 3.0 V	2.55	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH}$ or $V_{IL}$				
		$I_{\rm O}$ = 20 µA; $V_{\rm CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
VIH     H       VIL     L       VOH     H       VOH     L       VOH     L       I     I       IOFF     P       AlofF     P       ICC     S		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.33	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.33	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.45	V
l <sub>l</sub>	input leakage current	$V_I$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.5	μA
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.5	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μA
I <sub>CC</sub>	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A}; \\ V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
ΔI <sub>CC</sub>	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}; \text{ per pin}$ $^{[1]}$	-	-	50	μA

### Low-power dual 2-input NAND gate

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$T_{amb} = -40$	0 °C to +125 °C					
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	0.75 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.25 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	$0.30 \times V_{CC}$	V
V <sub>OH</sub>		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = -20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.11	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	$0.6 \times V_{CC}$	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	0.93	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.17	-	-	V
		$I_{\rm O}$ = -2.3 mA; $V_{\rm CC}$ = 2.3 V	1.77	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.67	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.40	-	-	V
		$I_{O}$ = -4.0 mA; $V_{CC}$ = 3.0 V	2.30	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 µA; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.33 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.41	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.39	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.36	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.50	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.50	V
I	input leakage current	$V_I$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.75	μA
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.75	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	$      V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V}; \\       V_{CC} = 0 \text{ V to } 0.2 \text{ V} $	-	-	±0.75	μA
I <sub>CC</sub>	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μA
ΔI <sub>CC</sub>	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ [1] $V_{CC} = 3.3 \text{ V}; \text{ per pin}$	-	-	75	μA

[1] One input at V\_{CC} - 0.6 V, other input at V\_{CC} or GND.

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# **11** Dynamic characteristics

#### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	ameter Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = -40 °C to +125 °C			Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 pF									
t <sub>pd</sub>	propagation	nA, nB to nY; see Figure 8 <sup>[2]</sup>							
	delay	V <sub>CC</sub> = 0.8 V	-	17.5	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.5	5.3	11.0	2.1	12.2	13.5	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.0	3.8	6.8	1.8	7.8	8.6	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.6	3.1	5.3	1.4	6.2	6.9	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.3	2.5	4.0	1.1	4.7	5.2	ns
		$V_{CC}$ = 3.0 V to 3.6 V	1.0	2.2	3.6	1.0	4.2	4.7	ns
C <sub>L</sub> = 10 p	F								
t <sub>pd</sub>	propagationd	nA, nB to nY; see Figure 8 [2]							
	elay	V <sub>CC</sub> = 0.8 V	-	21.0	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.4	6.1	13.0	2.2	14.4	15.9	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.4	4.4	7.9	2.2	9.2	10.2	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.0	3.7	6.2	1.9	7.3	8.1	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.4	3.0	4.7	1.3	5.6	6.2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.3	2.8	4.3	1.2	4.9	5.4	ns
C <sub>L</sub> = 15 p	F				<u> </u>	1			
t <sub>pd</sub>	propagation	nA, nB to nY; see Figure 8 <sup>[2]</sup>							
	delay	V <sub>CC</sub> = 0.8 V	-	24.5	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.4	6.9	14.8	3.1	16.5	18.2	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.8	5.0	8.9	2.5	10.5	11.6	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.0	4.1	7.0	2.0	8.3	9.2	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.7	3.5	5.3	1.5	6.4	7.1	ns
		$V_{CC}$ = 3.0 V to 3.6 V	1.6	3.2	4.9	1.4	5.7	6.3	ns
C <sub>L</sub> = 30 p	F			1	<u> </u>	1	1		
t <sub>pd</sub>	propagation	nA, nB to nY; see Figure 8 [2]							
	delay	V <sub>CC</sub> = 0.8 V	-	34.8	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	4.6	9.2	20.1	4.1	22.6	24.9	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.0	6.5	11.8	2.9	14.0	15.4	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.6	5.4	9.3	2.3	11.1	12.3	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.4	4.6	7.1	2.1	8.5	9.4	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.3	4.3	6.5	2.1	7.6	8.4	ns

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#### **Nexperia**

# 74AUP2G00

#### Low-power dual 2-input NAND gate

Symbol Parameter		Conditions	Ta	T <sub>amb</sub> = 25 °C		T <sub>amb</sub> = -40 °C to +125 °C			Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 pF	, 10 pF, 15 pF	and 30 pF							
	power	$f_i = 1 \text{ MHz}; V_i = \text{GND to } V_{CC}$	3]						
	dissipation capacitance	V <sub>CC</sub> = 0.8 V	-	2.8	-	-	-	-	pF
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	2.9	-	-	-	-	pF
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	3.0	-	-	-	-	pF
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	3.0	-	-	-	-	pF
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	3.4	-	-	-	-	pF
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	3.9	-	-	-	-	pF

All typical values are measured at nominal  $\ensuremath{\mathsf{V}_{\text{CC}}}$ 

[1] [2] [3]

 $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ . C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in µW).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

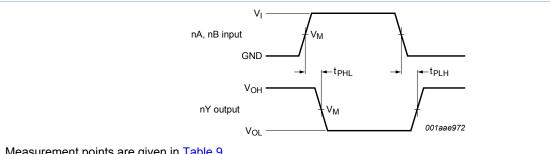
fo = output frequency in MHz;

 $C_L$  = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;  $\Sigma(C_L \times V_{CC}^2 \times f_0)$  = sum of outputs.

#### 11.1 Waveforms and test circuit



Measurement points are given in Table 9.

Logic levels:  $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

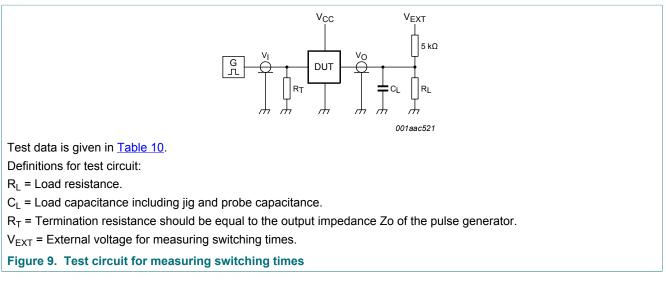
Figure 8. The data input (nA or nB) to output (nY) propagation delays

#### Table 9. Measurement points

Supply voltage	Output	Input		
V <sub>cc</sub>	V <sub>M</sub>	V <sub>M</sub>	VI	$t_r = t_f$
0.8 V to 3.6 V	0.5 × V <sub>CC</sub>	0.5 × V <sub>CC</sub>	V <sub>CC</sub>	≤ 3.0 ns

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#### Table 10. Test data

Supply voltage	Load		V <sub>EXT</sub>		
V <sub>cc</sub>	CL	R <sub>L</sub> <sup>[1]</sup>	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	2 × V <sub>CC</sub>

[1] For measuring enable and disable times  $R_L = 5 k\Omega$ .

For measuring propagation delays, setup and hold times and pulse width R<sub>L</sub> = 1 M $\Omega$ .

Low-power dual 2-input NAND gate

# 12 Package outline

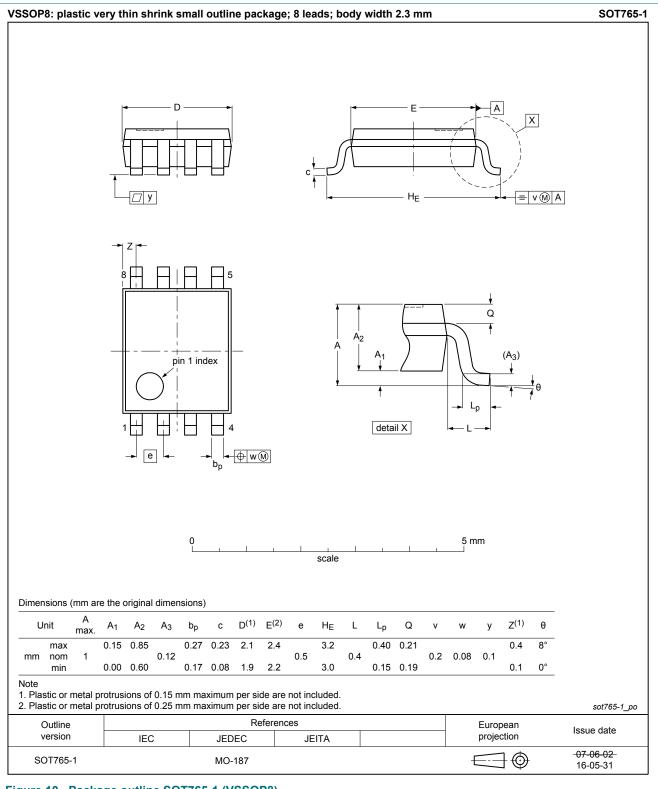
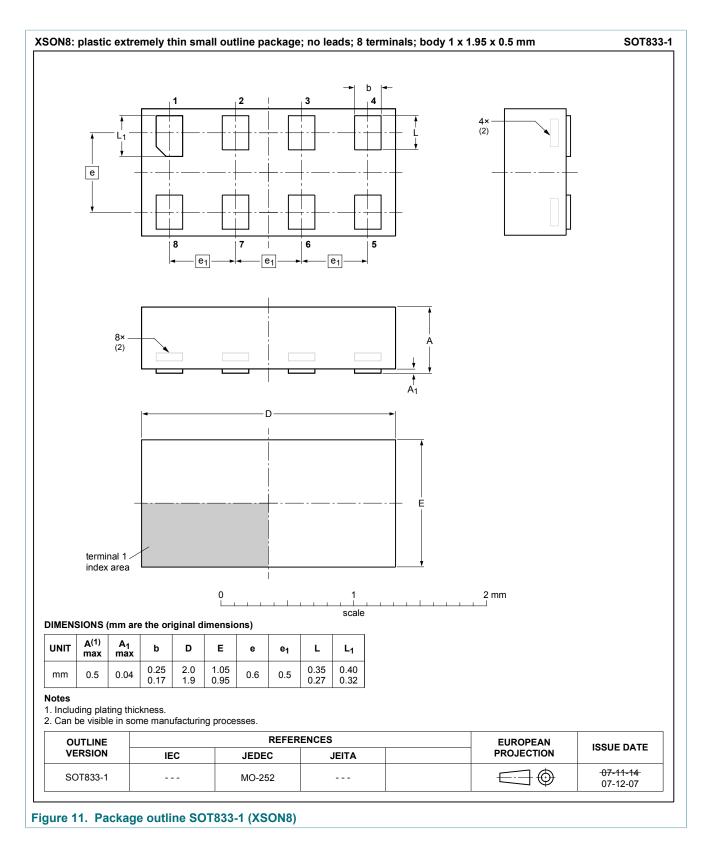


Figure 10. Package outline SOT765-1 (VSSOP8)

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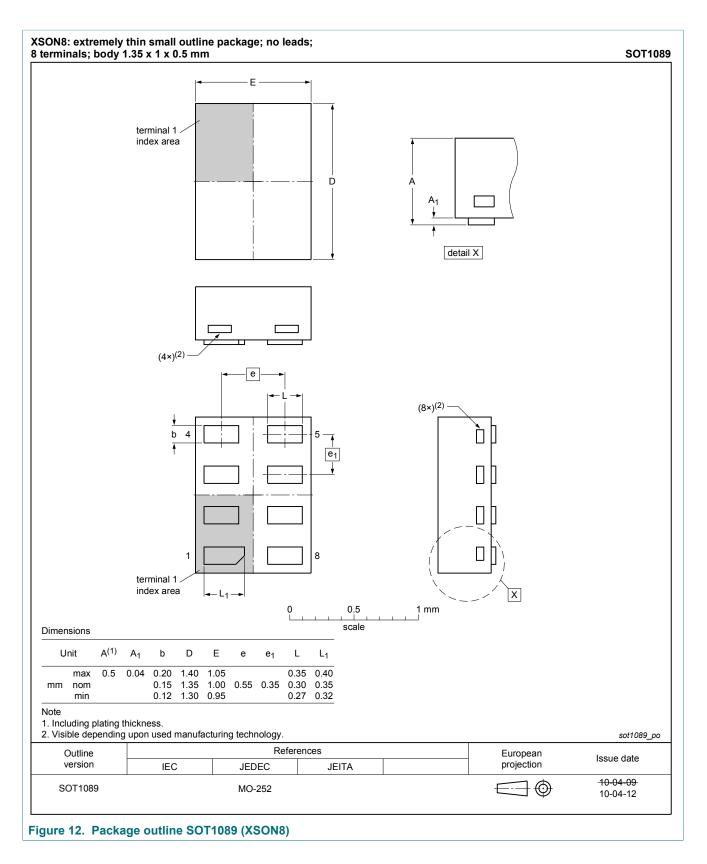
#### Low-power dual 2-input NAND gate



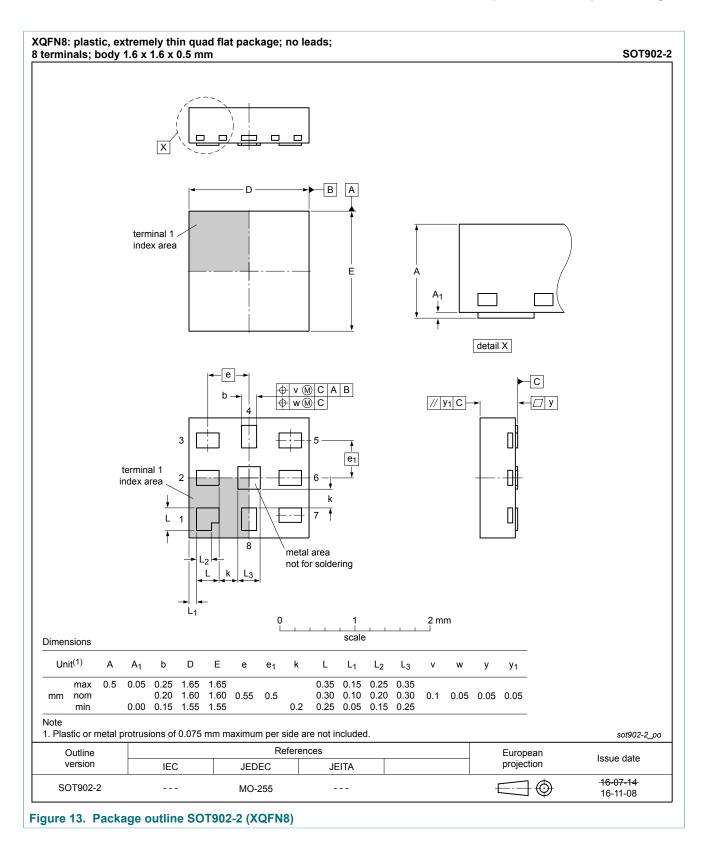
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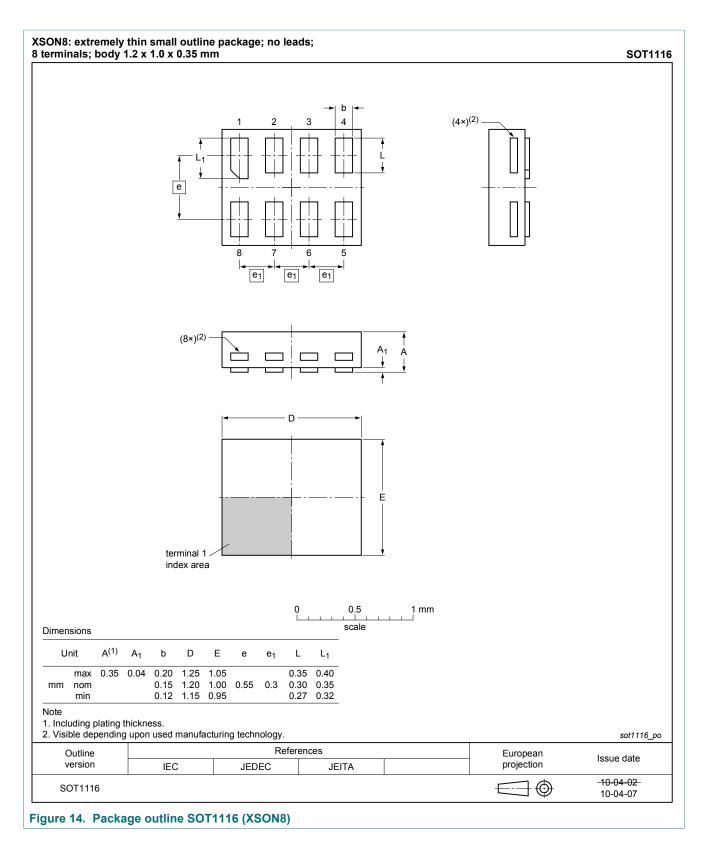
#### Low-power dual 2-input NAND gate



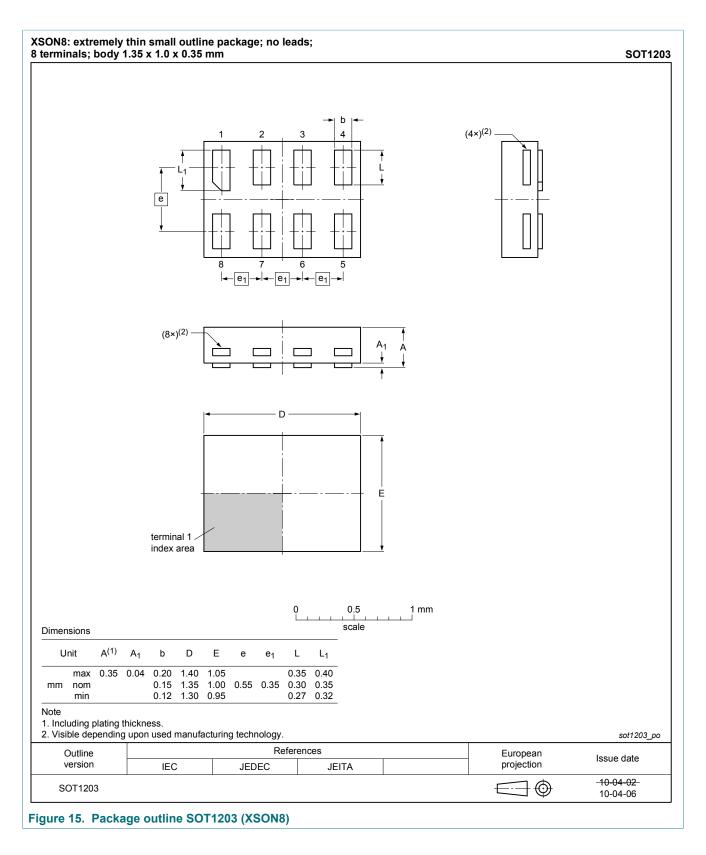
#### Low-power dual 2-input NAND gate



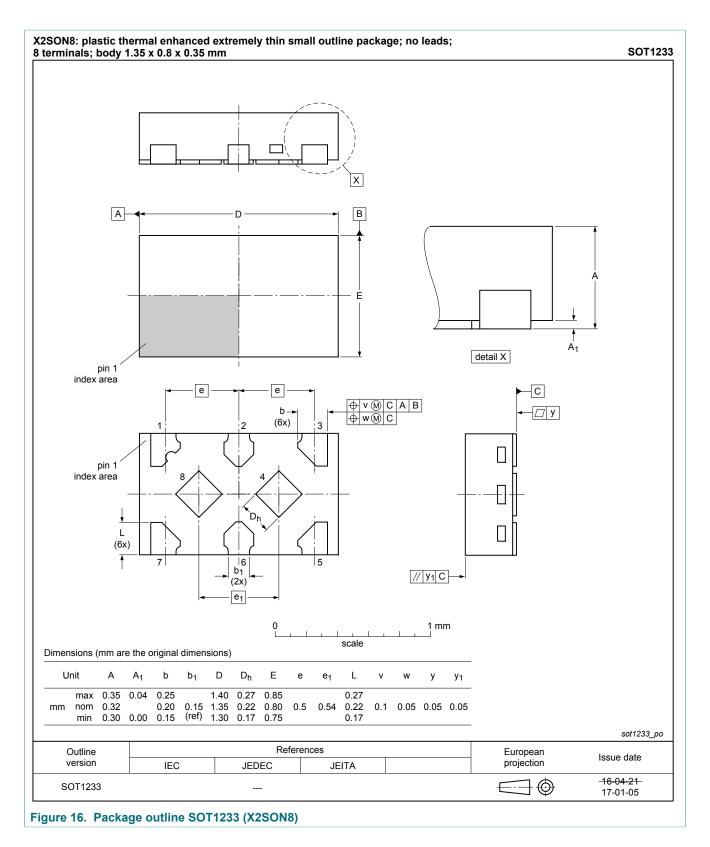
#### Low-power dual 2-input NAND gate



#### Low-power dual 2-input NAND gate



#### Low-power dual 2-input NAND gate



### **13 Abbreviations**

Table 11. Abbreviations			
Acronym	Description		
CDM	Charged Device Model		
DUT	Device Under Test		
ESD	ElectroStatic Discharge		
НВМ	Human Body Model		
ММ	Machine Model		

# 14 Revision history

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G00 v.10	20170703	Product data sheet	-	74AUP2G00 v.9
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Figure 7 and Figure 16 (drawings SOT1233/X2SON8) updated</li> <li>Type number 74AUP2G00GD removed.</li> </ul>			
74AUP2G00 v.9	20161028	Product data sheet	-	74AUP2G00 v.8
Modifications:	Added type number 74AUP2G00GX (SOT1233/X2SON8)			
74AUP2G00 v.8	20130205	Product data sheet	-	74AUP2G00 v.7
Modifications:	For type number 74AUP2G00GD XSON8U has changed to XSON8.			
74AUP2G00 v.7	20120608	Product data sheet	-	74AUP2G00 v.6
74AUP2G00 v.6	20111201	Product data sheet	-	74AUP2G00 v.5
74AUP2G00 v.5	20101021	Product data sheet	-	74AUP2G00 v.4
74AUP2G00 v.4	20080605	Product data sheet	-	74AUP2G00 v.3
74AUP2G00 v.3	20080403	Product data sheet	-	74AUP2G00 v.2
74AUP2G00 v.2	20070515	Product data sheet	-	74AUP2G00 v.1
74AUP2G00 v.1	20060825	Product data sheet	-	-

### 15 Legal information

#### 15.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

Please consult the most recently issued document before initiating or completing a design. [1]

The term 'short data sheet' is explained in section "Definitions".

[2] [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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